A B S T R A C T

The content of zinc compounds in the polishing pad used for mirror-polishing a semiconductor wafer is 200ppm or less at the ratio of zinc weight relative to the weight of the polishing pad, preferably 100ppm or less, more preferably the polishing pad does not include zinc compounds. Preferably, the polishing pad comprises a base layer formed of nonwoven fabric, and a porous surface layer which is more preferably formed of foamed polyurethane, and the content of zinc compounds in the surface layer is 100ppm or less. There is provided a polishing pad and polishing method for producing a mirror-polished wafer in the case of a mirror polishing, especially a finish polishing without the generation of polishing damages in the polishing process.

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